CS92-2M
CS92-2N*

SILICON CONTROLLED RECTIFIER
2.0 AMP, 600 THRU 800 VOLTS

TO-92 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CS92-2M and CS92-2N are epoxy molded Silicon Controlled Rectifiers designed for sensing circuit applications and control systems.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C unless otherwise noted)

	SYMBOL	CS92-2M	CS92-2N*	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	600	800	V
RMS On-State Current (T_C=60°C)	$I_{T(RMS)}$	2.0		A
Peak One Cycle Surge (t=10ms)	I_{TSM}	10		A
I^2t Value for Fusing (t=10ms)	I^2t	0.24		A^2s
Peak Gate Power (tp=10μs)	P_{GM}	2.0		W
Average Gate Power Dissipation	$P_{G\ (AV)}$	0.1		W
Peak Gate Current (tp=10μs)	I_{GM}	1.0		A
Peak Gate Voltage (tp=10μs)	V_{GM}	8.0		V
Storage Temperature	T_{stg}	-40 to +150		°C
Junction Temperature	T_J	-40 to +125		°C
Thermal Resistance	Θ_{JA}	200		°C/W
Thermal Resistance	Θ_{JC}	100		°C/W

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated V_{DRM}, V_{RRM}, R_{GK}=1KΩ			10	μA
I_{DRM}, I_{RRM}	Rated V_{DRM}, V_{RRM}, R_{GK}=1KΩ, T_C=125°C			100	μA
I_{GT}	V_D=12V		20	200	μA
I_H	I_T=100mA, R_{GK}=1KΩ			2.0	mA
V_{GT}	V_D=12V			0.8	V
V_{TM}	I_{TM}=4.0A, tp=380μs		1.4	1.7	V
dv/dt	V_D=$^2/_3$ V_{DRM}, R_{GK}=1KΩ, T_C=125°C	10			V/μs

* Available on request. Please consult factory.

R0 (22-April 2004)

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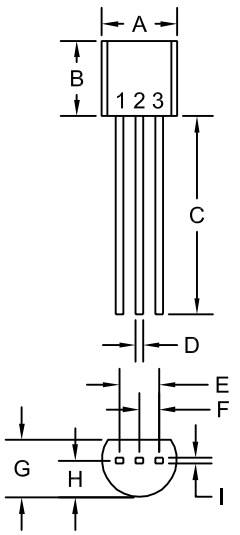
TO-92 CASE - MECHANICAL OUTLINE



R1

LEAD CODE:
1) CATHODE
2) GATE
3) ANODE

MARKING CODE:
FULL PART NUMBER

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R0 (22-April 2004)